











CSD17570Q5B

SLPS471D - FEBRUARY 2014-REVISED MAY 2017

# CSD17570Q5B 30 V N-Channel NexFET™ Power MOSFET

### **Features**

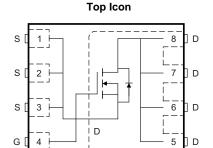
- Ultra-Low Resistance
- Low Thermal Resistance
- Avalanche Rated
- Pb Free Terminal Plating
- **RoHS Compliant**
- Halogen Free
- SON 5 mm × 6 mm Plastic Package

## Applications

ORing and Hot Swap Applications

## 3 Description

This 30 V, 0.56 m $\Omega$ , SON 5 × 6 mm NexFET<sup>TM</sup> power MOSFET is designed to minimize resistance for ORing and hot swap applications and is not intended for switching applications.



#### **Product Summary**

$T_A = 25^\circ$	С	TYPICAL VA	UNIT	
$V_{DS}$	Drain-to-Source Voltage	30		٧
$Q_g$	Gate Charge Total (4.5 V)	93		nC
$Q_{gd}$	Gate Charge Gate-to-Drain	34	nC	
D	Drain-to-Source On-Resistance	V <sub>GS</sub> = 4.5 V	0.74	mΩ
R <sub>DS(on)</sub>	Drain-to-Source On-Resistance	V <sub>GS</sub> = 10 V 0.56		mΩ
V <sub>GS(th)</sub>	Threshold Voltage	1.5		V

## Ordering Information<sup>(1)</sup>

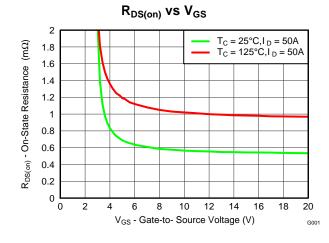
Device	Qty	Media	Package	Ship
CSD17570Q5B	2500	13-Inch Reel	SON 5 x 6 mm	Tape and
CSD17570Q5BT	250	7-Inch Reel	Plastic Package	Reel

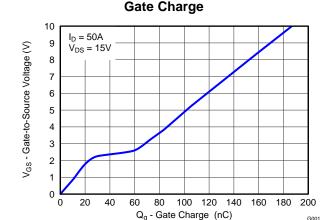
For all available packages, see the orderable addendum at the end of the data sheet.

### **Absolute Maximum Ratings**

T <sub>A</sub> = 2	5°C	VALUE	UNIT
$V_{DS}$	Drain-to-Source Voltage	30	٧
$V_{GS}$	Gate-to-Source Voltage	±20	٧
	Continuous Drain Current (Package limited)	100	
I <sub>D</sub>	Continuous Drain Current (Silicon limited), $T_C = 25^{\circ}C$	407	Α
	Continuous Drain Current, T <sub>A</sub> = 25°C <sup>(1)</sup>	53	
$I_{DM}$	Pulsed Drain Current, T <sub>A</sub> = 25°C <sup>(2)</sup>	400	Α
$P_D$	Power Dissipation <sup>(1)</sup>	3.2	W
$T_J$ , $T_{stg}$	Operating Junction and Storage Temperature Range	-55 to 150	°C
E <sub>AS</sub>	Avalanche Energy, single pulse $I_D$ = 90 A, L = 0.1 mH, $R_G$ = 25 $\Omega$	450	mJ

- (1) Typical  $R_{\theta JA} = 40^{\circ}\text{C/W}$  on a 1 inch<sup>2</sup>, 2 oz. Cu pad on a 0.06 inch thick FR4 PCB.
- (2) Pulse duration ≤100 μs, duty cycle ≤2%







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# 4 Revision History

Changes from Revision C (January 2015) to Revision D	Page
Added the Receiving Notification of Documentation Updates and Community Resources sections to Device and Documentation Support.	
Changed the dimension between pads 3 and 4 from 0.028 inches: to 0.050 inches in the Recommended PCB Pattern section diagram	
Changes from Revision B (August 2014) to Revision C	Page
Corrected Pulsed Drain Current to read 400 A.	1
Changes from Revision A (May 2014) to Revision B	Page
• Updated Figure 1 to state Max R <sub>θJC</sub> = 0.8°C/W.	
Updated the SOA in Figure 10.	6
Changes from Original (February 2014) to Revision A	Page
Undated the mechanical drawing	8

Product Folder Links: CSD17570Q5B



# 5 Specifications

### 5.1 Electrical Characteristics

 $(T_A = 25^{\circ}C \text{ unless otherwise stated})$ 

	PARAMETER	TEST CONDITIONS	MIN T	YP MAX	UNIT
STATIC	CHARACTERISTICS		<u>'</u>		
BV <sub>DSS</sub>	Drain-to-Source Voltage	V <sub>GS</sub> = 0 V, I <sub>D</sub> = 250 μA	30		V
I <sub>DSS</sub>	Drain-to-Source Leakage Current	V <sub>GS</sub> = 0 V, V <sub>DS</sub> = 24 V		1	μА
I <sub>GSS</sub>	Gate-to-Source Leakage Current	V <sub>DS</sub> = 0 V, V <sub>GS</sub> = 20 V		100	nA
V <sub>GS(th)</sub>	Gate-to-Source Threshold Voltage	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 250 μA	1.1	1.5 1.9	V
D	Dunin to Course On Benintanno	V <sub>GS</sub> = 4.5 V, I <sub>D</sub> = 50 A	0	.74 0.92	mΩ
R <sub>DS(on)</sub>	Drain-to-Source On-Resistance	V <sub>GS</sub> = 10 V, I <sub>D</sub> = 50 A	0	.56 0.69	mΩ
9 <sub>fs</sub>	Transconductance	V <sub>DS</sub> = 15 V, I <sub>D</sub> = 50 A	:	271	S
DYNAMI	IC CHARACTERISTICS				•
C <sub>iss</sub>	Input Capacitance		104	400 13600	pF
C <sub>oss</sub>	Output Capacitance	$V_{GS} = 0 \text{ V}, V_{DS} = 15 \text{ V}, f = 1 \text{ MHz}$	14	150 1890	pF
C <sub>rss</sub>	Reverse Transfer Capacitance		8	377 1140	pF
R <sub>G</sub>	Series Gate Resistance			1.8 3.6	Ω
Qg	Gate Charge Total (4.5 V)			93 121	nC
Q <sub>gd</sub>	Gate Charge Gate-to-Drain	V 45.V 1 50.A		34	nC
Q <sub>gs</sub>	Gate Charge Gate-to-Source	V <sub>DS</sub> = 15 V, I <sub>D</sub> = 50 A		27	nC
Q <sub>g(th)</sub>	Gate Charge at V <sub>th</sub>			17	nC
Q <sub>oss</sub>	Output Charge	V <sub>DS</sub> = 15 V, V <sub>GS</sub> = 0 V		40	nC
t <sub>d(on)</sub>	Turn On Delay Time			5	ns
t <sub>r</sub>	Rise Time	V <sub>DS</sub> = 15 V, V <sub>GS</sub> = 10 V,		36	ns
t <sub>d(off)</sub>	Turn Off Delay Time	$I_{DS} = 50 \text{ A}, R_G = 0 \Omega$		144	ns
t <sub>f</sub>	Fall Time			74	ns
DIODE (	CHARACTERISTICS				•
V <sub>SD</sub>	Diode Forward Voltage	I <sub>SD</sub> = 50 A, V <sub>GS</sub> = 0 V		0.8 1	V
Q <sub>rr</sub>	Reverse Recovery Charge	V <sub>DS</sub> = 15 V, I <sub>F</sub> = 50 A,		34	nC
t <sub>rr</sub>	Reverse Recovery Time	di/dt = 300 A/μs		51	ns

## 5.2 Thermal Information

(T<sub>A</sub> = 25°C unless otherwise stated)

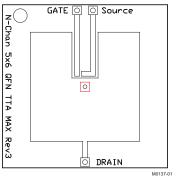
	THERMAL METRIC	MIN	TYP	MAX	UNIT
$R_{\theta JC}$	Junction-to-Case Thermal Resistance <sup>(1)</sup>			0.8	°C/W
$R_{\theta JA}$	Junction-to-Ambient Thermal Resistance <sup>(1)(2)</sup>			50	C/VV

<sup>(1)</sup> R<sub>θJC</sub> is determined with the device mounted on a 1 inch² (6.45 cm²), 2 oz. (0.071 mm thick) Cu pad on a 1.5 inches x 1.5 inches (3.81 cm x 3.81 cm), 0.06 inch (1.52 mm) thick FR4 PCB. R<sub>θJC</sub> is specified by design, whereas R<sub>θJA</sub> is determined by the user's board design.

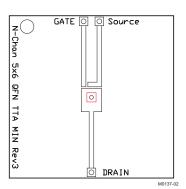
(2) Device mounted on FR4 material with 1 inch<sup>2</sup> (6.45 cm<sup>2</sup>), 2 oz. (0.071 mm thick) Cu.

Product Folder Links: CSD17570Q5B





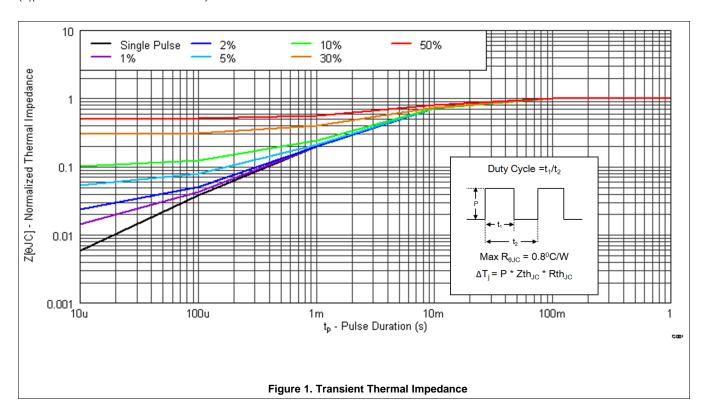
Max  $R_{\theta JA} = 50^{\circ} C/W$  when mounted on 1 inch<sup>2</sup> (6.45 cm<sup>2</sup>) of 2 oz. (0.071 mm thick) Cu.



Max  $R_{\theta JA} = 125^{\circ} C/W$  when mounted on a minimum pad area of 2 oz. (0.071 mm thick) Cu.

## 5.3 Typical MOSFET Characteristics

(T<sub>A</sub> = 25°C unless otherwise stated)



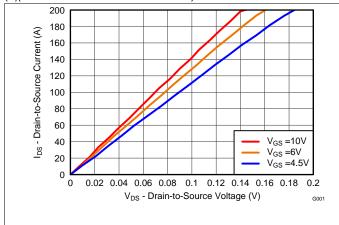
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## **Typical MOSFET Characteristics (continued)**

(T<sub>A</sub> = 25°C unless otherwise stated)



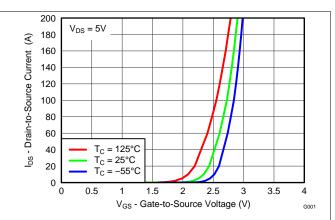
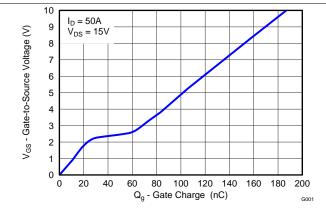


Figure 2. Saturation Characteristics





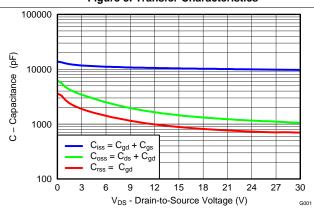


Figure 4. Gate Charge

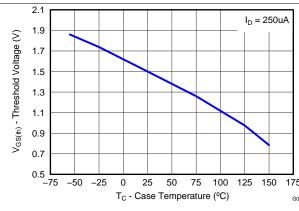


Figure 6. Threshold Voltage vs Temperature

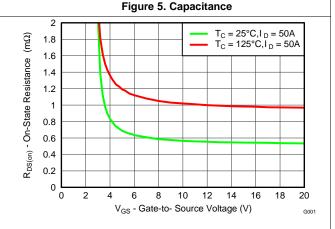
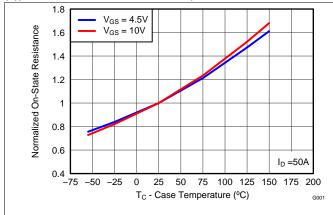


Figure 7. On-State Resistance vs Gate-to-Source Voltage



## **Typical MOSFET Characteristics (continued)**

(T<sub>A</sub> = 25°C unless otherwise stated)



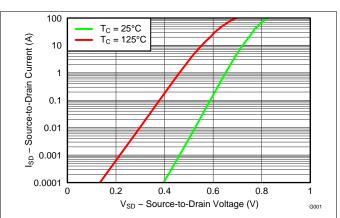
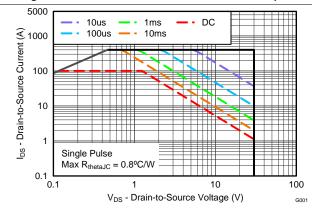


Figure 8. Normalized On-State Resistance vs Temperature





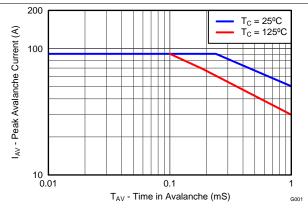


Figure 10. Maximum Safe Operating Area



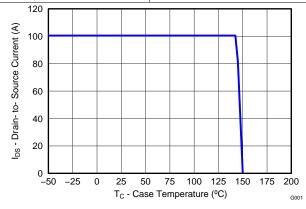


Figure 12. Maximum Drain Current vs Temperature

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## 6 Device and Documentation Support

### 6.1 Receiving Notification of Documentation Updates

To receive notification of documentation updates, navigate to the device product folder on ti.com. In the upper right corner, click on *Alert me* to register and receive a weekly digest of any product information that has changed. For change details, review the revision history included in any revised document.

### 6.2 Community Resources

The following links connect to TI community resources. Linked contents are provided "AS IS" by the respective contributors. They do not constitute TI specifications and do not necessarily reflect TI's views; see TI's Terms of Use.

TI E2E™ Online Community TI's Engineer-to-Engineer (E2E) Community. Created to foster collaboration among engineers. At e2e.ti.com, you can ask questions, share knowledge, explore ideas and help solve problems with fellow engineers.

**Design Support** *TI's Design Support* Quickly find helpful E2E forums along with design support tools and contact information for technical support.

#### 6.3 Trademarks

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#### 6.4 Electrostatic Discharge Caution



These devices have limited built-in ESD protection. The leads should be shorted together or the device placed in conductive foam during storage or handling to prevent electrostatic damage to the MOS gates.

## 6.5 Glossary

SLYZ022 — TI Glossary.

This glossary lists and explains terms, acronyms, and definitions.

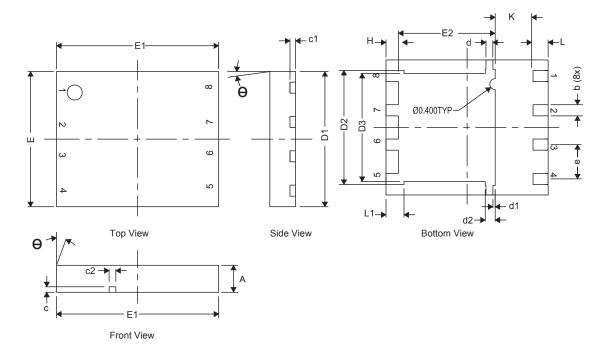
Product Folder Links: CSD17570Q5B



## 7 Mechanical, Packaging, and Orderable Information

The following pages include mechanical, packaging, and orderable information. This information is the most current data available for the designated devices. This data is subject to change without notice and revision of this document. For browser-based versions of this data sheet, refer to the left-hand navigation.

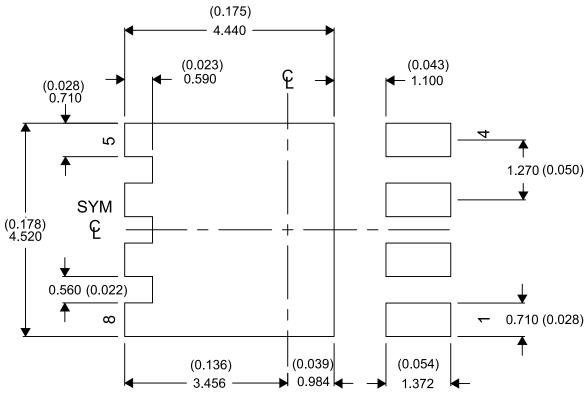
## 7.1 Q5B Package Dimensions



DIM	MILLIMETERS							
DIIVI	MIN	NOM	MAX					
Α	0.80	1.00	1.05					
b	0.36	0.41	0.46					
С	0.15	0.20	0.25					
c1	0.15	0.20	0.25					
c2	0.20	0.25	0.30					
D1	4.90	5.00	5.10					
D2	4.12	4.22	4.32					
D3	3.90	4.00	4.10					
d	0.20	0.25	0.30					
d1		0.085 TYP						
d2	0.319	0.369	0.419					
E	4.90	5.00	5.10					
E1	5.90	6.00	6.10					
E2	3.48	3.58	3.68					
е		1.27 TYP						
Н	0.36	0.46	0.56					
L	0.46	0.56	0.66					
L1	0.57	0.67	0.77					
θ	0°	_	_					
K		1.40 TYP						

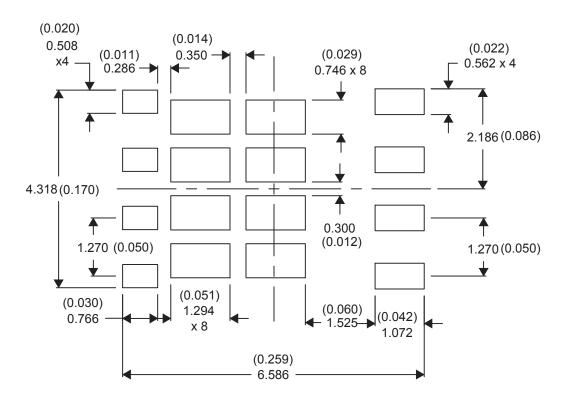


### 7.2 Recommended PCB Pattern



For recommended circuit layout for PCB designs, see application note SLPA005 – Reducing Ringing Through PCB Layout Techniques.

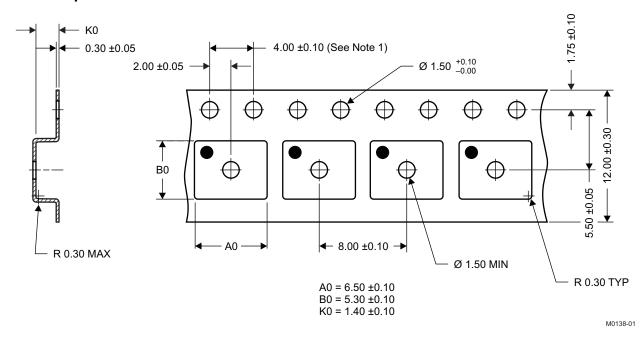
## 7.3 Recommended Stencil Pattern



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## 7.4 Q5B Tape and Reel Information



### Notes:

- 1. 10-sprocket hole-pitch cumulative tolerance ±0.2
- 2. Camber not to exceed 1 mm in 100 mm, noncumulative over 250 mm
- 3. Material: black static-dissipative polystyrene
- 4. All dimensions are in mm (unless otherwise specified).
- 5. A0 and B0 measured on a plane 0.3 mm above the bottom of the pocket.



## PACKAGE OPTION ADDENDUM

18-May-2017

#### **PACKAGING INFORMATION**

Orderable Device	Status	Package Type	_	Pins	_	Eco Plan	Lead/Ball Finish	MSL Peak Temp	Op Temp (°C)	Device Marking	Samples
	(1)		Drawing		Qty	(2)	(6)	(3)		(4/5)	
CSD17570Q5B	ACTIVE	VSON-CLIP	DNK	8	2500	Pb-Free (RoHS Exempt)	CU NIPDAU   CU SN	Level-1-260C-UNLIM		CSD17570	Samples
CSD17570Q5BT	ACTIVE	VSON-CLIP	DNK	8	250	Pb-Free (RoHS Exempt)	CU NIPDAU   CU SN	Level-1-260C-UNLIM		CSD17570	Samples

(1) The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

**OBSOLETE:** TI has discontinued the production of the device.

(2) RoHS: TI defines "RoHS" to mean semiconductor products that are compliant with the current EU RoHS requirements for all 10 RoHS substances, including the requirement that RoHS substance do not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, "RoHS" products are suitable for use in specified lead-free processes. TI may reference these types of products as "Pb-Free".

RoHS Exempt: TI defines "RoHS Exempt" to mean products that contain lead but are compliant with EU RoHS pursuant to a specific EU RoHS exemption.

**Green:** TI defines "Green" to mean the content of Chlorine (CI) and Bromine (Br) based flame retardants meet JS709B low halogen requirements of <=1000ppm threshold. Antimony trioxide based flame retardants must also meet the <=1000ppm threshold requirement.

- (3) MSL, Peak Temp. The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.
- (4) There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.
- (5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.
- (6) Lead/Ball Finish Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead/Ball Finish values may wrap to two lines if the finish value exceeds the maximum column width.

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